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	U	Document ID	Issue Da	Page	Title	Current OR	Current XR	Retrieval	Inventor	S	C
46	<input type="checkbox"/>	US 6743672 B2	20040601	9	Method for manufacturing a capaci	438/253	438/256; 438/396		Park, Jong-Bum	<input checked="" type="checkbox"/>	<input type="checkbox"/>
47	<input type="checkbox"/>	US 6734061 B2	20040511	15	Semiconductor memory device having a plug c	438/253	257/296; 257/306;		Hong, Kwon et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
48	<input type="checkbox"/>	US 6727156 B2	20040427	15	Semiconductor device including ferroelectri	438/396	257/295; 257/310;		Jung, Dong-jin et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
49	<input type="checkbox"/>	US 6724034 B2	20040420	53	Semiconductor integrated circuit dev	257/310	257/296; 257/306;		Iijima, Shinpei et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
50	<input type="checkbox"/>	US 6720603 B2	20040413	149	CAPACITOR STRUCTURE AND A SEMICONDUCTOR DE	257/303	257/306; 257/310;		Iijima, Shinpei et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
51	<input type="checkbox"/>	US 6720232 B1	20040413	23	Method of fabricating an embedded DRAM for m	438/396	257/296; 257/306;		Tu, Kuo-Chi et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
52	<input type="checkbox"/>	US 6709919 B2	20040323	21	Method for making auto-self-aligned top	438/255	438/253; 438/396;		Tu, Kuo-Chi	<input checked="" type="checkbox"/>	<input type="checkbox"/>
53	<input type="checkbox"/>	US 6693015 B2	20040217	22	Method for improved processing and etchbac	438/306	257/E21.01 9;		Carstensen, Robert K.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
54	<input type="checkbox"/>	US 6686235 B2	20040203	30	Buried digit spacer-separated capac	438/239	257/E27.04 8;		Clampitt, Darwin A.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
55	<input type="checkbox"/>	US 6680502 B2	20040120	29	Buried digit spacer separated capacitor ar	257/296	257/288; 257/908;		Clampitt, Darwin A.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
56	<input type="checkbox"/>	US 6660580 B2	20031209	19	Capacitor of an integrated circuit dev	438/240	438/244; 438/253;		Lee, Kong-Soo	<input checked="" type="checkbox"/>	<input type="checkbox"/>
57	<input type="checkbox"/>	US 6656789 B2	20031202	11	Capacitor for highly-integrated semi	438/253	257/E21.00 8;		Lee, Kee Jeung et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
58	<input type="checkbox"/>	US 6642097 B2	20031104	19	Structure for capacitor-top-plate to	438/241	438/253; 438/255		Tu, Kuo-Chi	<input checked="" type="checkbox"/>	<input type="checkbox"/>
59	<input type="checkbox"/>	US 6627938 B2	20030930	12	Capacitor constructions	257/301	257/303; 257/304;		Kwok, Siang Ping et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
60	<input type="checkbox"/>	US 6624018 B1	20030923	14	Method of fabricating a DRAM device featurin	438/239	257/E21.01 6;		Yu, Chih-Hsing et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
61	<input type="checkbox"/>	US 6623988 B2	20030923	11	Method for fabricating ferroelectric capacito	438/3	257/E21.00 9;		Park, Won Kyu	<input checked="" type="checkbox"/>	<input type="checkbox"/>
62	<input type="checkbox"/>	US 6620672 B1	20030916	17	SOI DRAM with buried capacitor under the di	438/239	438/142; 438/147;		Dennison, Charles H. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
63	<input type="checkbox"/>	US 6599799 B2	20030729	14	Double sided container capacitor for DRAM cel	438/253	257/E21.01 9;		Tang, Sanh D. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>
64	<input type="checkbox"/>	US 6589876 B1	20030708	15	Methods of forming	438/700	257/E21.64 0;		Tran, Luan C.	<input checked="" type="checkbox"/>	<input type="checkbox"/>

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135	<input type="checkbox"/>	US 6080622	20000627	6	Method for fabricating a DRAM cell capacitor	438/253	257/306;		Kang, Woo-Tag	<input type="checkbox"/> <input type="checkbox"/>
136	<input type="checkbox"/>	US 6078493	20000620	17	Fin-shaped capacitor	361/303	257/E21.64		Kang, Chang-seok	<input type="checkbox"/> <input type="checkbox"/>
137	<input type="checkbox"/>	US 6071773	20000606	13	Process for fabricating a DRAM met	438/253	257/308;		Lee, Jin-Yuan et al.	<input type="checkbox"/> <input type="checkbox"/>
138	<input type="checkbox"/>	US 6066541	20000523	12	Method for fabricating a cylindrical capacitor	438/397	438/235;		Hsieh, Ming-Teng et al.	<input type="checkbox"/> <input type="checkbox"/>
139	<input type="checkbox"/>	US 6066528	20000523	32	Method for forming a capacitor compatible w	438/253	438/238;		Fazan, Pierre C. et al.	<input type="checkbox"/> <input type="checkbox"/>
140	<input type="checkbox"/>	US 6060353	20000509	9	Method of forming a ring shaped storage no	438/253	257/E21.01		Koh, Chao-Ming	<input type="checkbox"/> <input type="checkbox"/>
141	<input type="checkbox"/>	US 6060351	20000509	14	Process for forming capacitor over bit lin	438/253	257/E21.01		Parekh, Kunal R. et al.	<input type="checkbox"/> <input type="checkbox"/>
142	<input type="checkbox"/>	US 6054347	20000425	16	Method for forming a modified crown shaped	438/253	257/E21.64		Lin, Chin-Hsiang	<input type="checkbox"/> <input type="checkbox"/>
143	<input type="checkbox"/>	US 6046083	20000404	10	Growth enhancement of hemispherical grain si	438/255	257/532;		Lin, Dahcheng et al.	<input type="checkbox"/> <input type="checkbox"/>
144	<input type="checkbox"/>	US 6034392	20000307	21	Semiconductor device having capacitor	257/306	257/534;		Joo, Jae-Hyun	<input type="checkbox"/> <input type="checkbox"/>
145	<input type="checkbox"/>	US 6025247	20000215	26	Method for manufacturing capacitor	438/396	257/E21.01		Chang, Julian Y. et al.	<input type="checkbox"/> <input type="checkbox"/>
146	<input type="checkbox"/>	US 6025227	20000215	13	Capacitor over bit line structure using a	438/253	257/E21.64		Sung, Janmye	<input type="checkbox"/> <input type="checkbox"/>
147	<input type="checkbox"/>	US 6020248	20000201	18	Method for fabricating semiconductor device b	438/398	257/E21.01		Zenke, Masanobu	<input type="checkbox"/> <input type="checkbox"/>
148	<input type="checkbox"/>	US 6015734	20000118	12	Method for improving the yield on dynamic r	438/253	257/E21.64		Huang, Kuo Ching et al.	<input type="checkbox"/> <input type="checkbox"/>
149	<input type="checkbox"/>	US 6010942	20000104	10	Post chemical mechanical polishing	438/396	257/E21.01		Chien, Rong-Wu et al.	<input type="checkbox"/> <input type="checkbox"/>
150	<input type="checkbox"/>	US 6008085	19991228	13	Design and a novel process for formation	438/253	257/E21.64		Sung, Janmye et al.	<input type="checkbox"/> <input type="checkbox"/>
151	<input type="checkbox"/>	US 5989954	19991123	11	Method for forming a cylinder capacitor in	438/253	257/E21.64		Lee, Yu-Hua et al.	<input type="checkbox"/> <input type="checkbox"/>
152	<input type="checkbox"/>	US 5972770	19991026	15	Method of manufacturing a DRAM c	438/396	438/253		Hsu, Chen-Chung	<input type="checkbox"/> <input type="checkbox"/>
153	<input type="checkbox"/>	US 5960280	19990928	12	Method of fabricating	438/254	257/E21.01		Jenq, Jason et	<input type="checkbox"/> <input type="checkbox"/>